

## IN THE CLAIMS

1. (Canceled)
2. (Currently amended) The method of claim 1 6 comprising:  
depositing a conductive layer to fill the trench; and  
removing a portion of the conductive layer stacked on a top surface of the organic silicon oxide layer by chemical-mechanical polishing (CMP).
3. (Currently amended) The method of claim 1 6 comprising:  
forming a photo resist pattern exposing a predetermined portion of a bottom of the trench after forming the trench; and  
forming a contact hole by etching the inorganic silicon oxide layer with the photo resist pattern.
4. (Currently amended) The method of claim 1 6 wherein the ~~oxygenation~~ oxygenating includes ashing the photo resist pattern formed during the patterning step.
5. (Currently amended) The method of claim 16 wherein the oxygenation is performed at a region having a thickness less than 1000 Å in an exposed region of the organic silicon oxide layer.
6. (Previously presented) A method for fabricating a semiconductor device, comprising:  
depositing an inorganic silicon oxide layer on a substrate;  
sequentially depositing an organic silicon oxide layer of a low dielectric constant on the inorganic silicon oxide layer;  
forming a partial trench with a predetermined depth in the organic silicon oxide layer;  
oxygenating an inner wall of the partial trench; and  
forming a trench by etching the partial trench with hydrofluoric acid (HF) for about 5 seconds using a buffered oxide etchant (BOE).
- 7-15 (Canceled)